

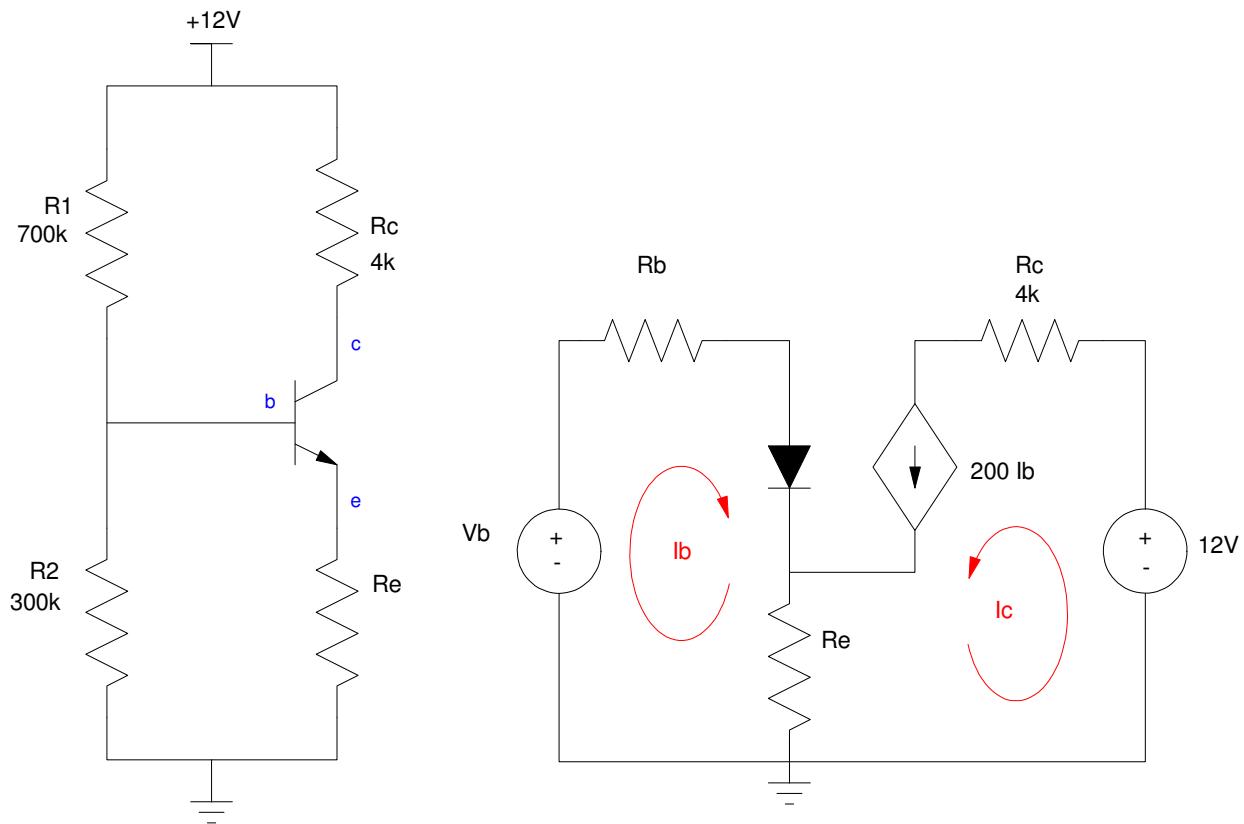
ECE 321 - Quiz #5 - Name _____

BJT Amplifiers. Due midnight, April 6th

1) BJT Amplifier: DC Analysis. Determine the Thevenin equivalent of R₁ and R₂ as well as the Q-point.
Assume ideal silicon transistors:

- |V_{be}| = 0.7V
- $\beta = 200$
- $R_e = 1000 + 100 \cdot (\text{your birth month}) + (\text{your birth day})$. May 14th would give $R = 1514$ Ohms

R_e $1000 + 100 \cdot \text{mo} + \text{day}$	V_b	R_b	V_{ce}	I_c



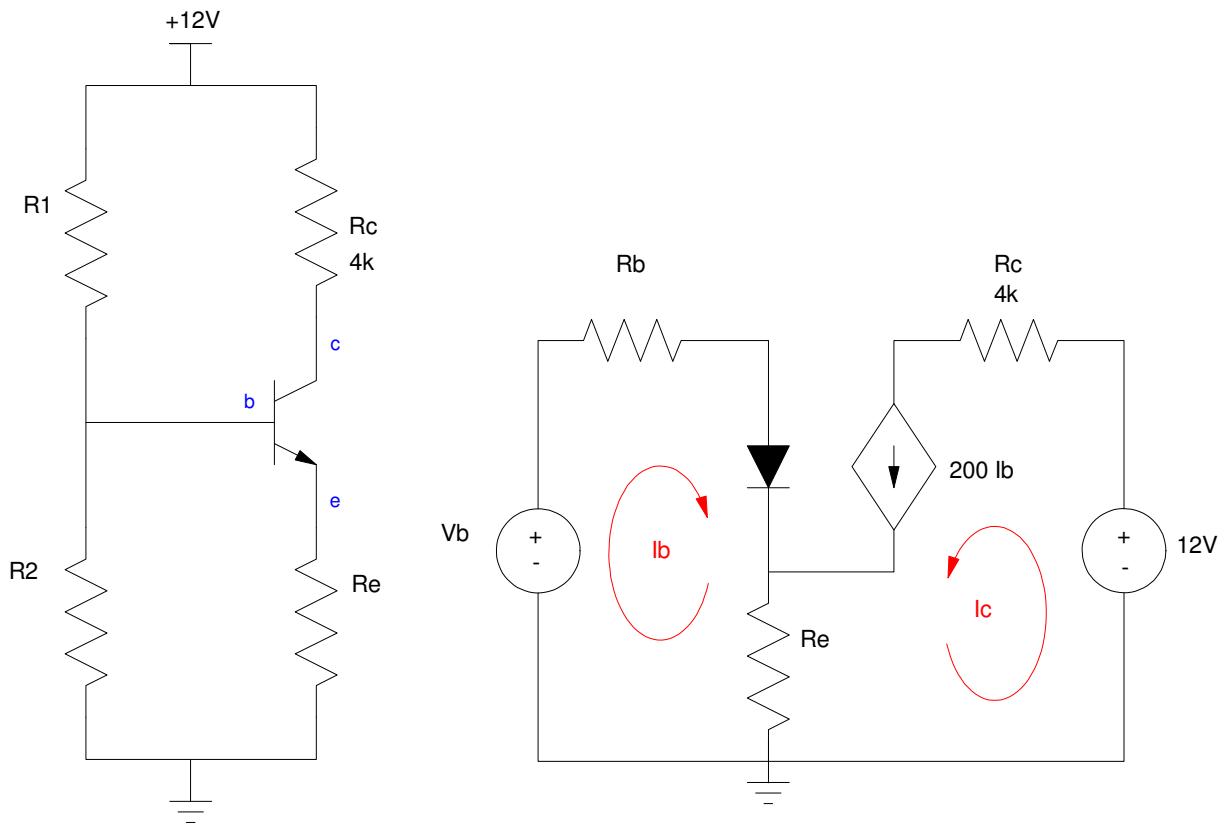
2) BJT Amplifier: DC Design. Determine R1 and R2 so that

- The Q point is $V_{ce} = 6.00V$ and
- The Q point is stabilized for variations in β

Assume

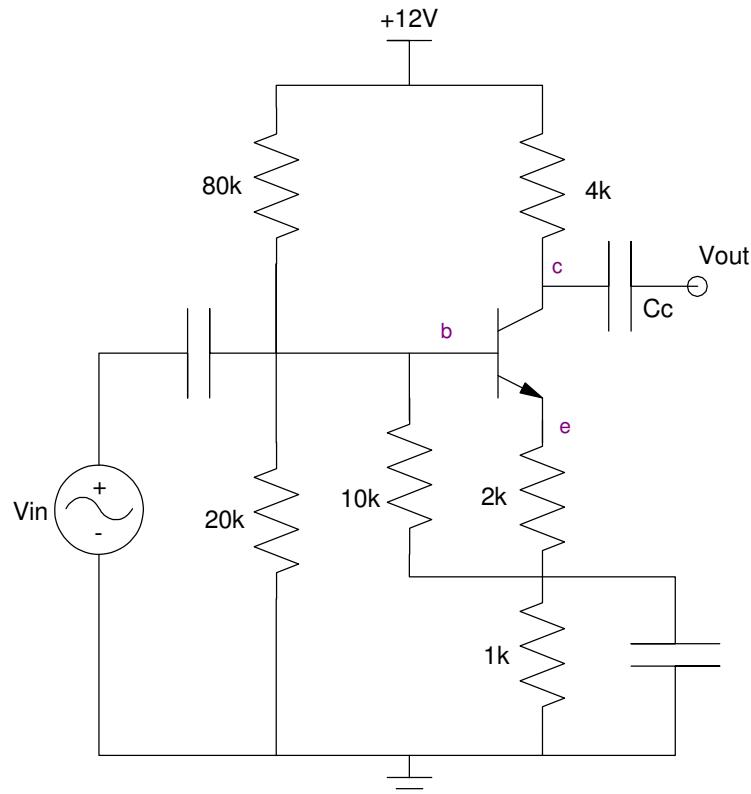
- Ideal silicon transistors ($V_{be} = 0.7V$, $\beta = 200$)
- $R_e = 1000 + 100 \cdot (\text{birth month}) + (\text{birth day})$. May 14th gives $R_e = 1514 \Omega$

R_e $1000 + 100 \cdot \text{mo} + \text{day}$	R_1	R_2	V_b	R_b



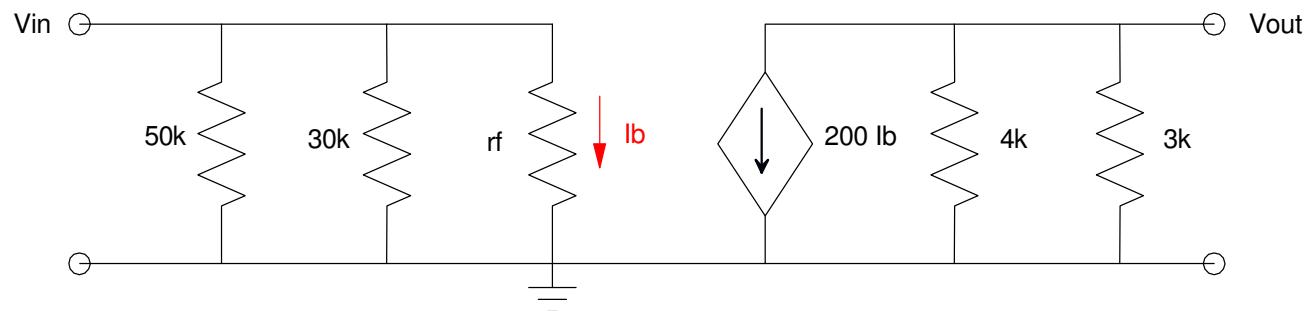
3) BJT: AC Analysis: Draw the small signal model for the following BJT amplifier. Assume

- $r_f = 3000\Omega$
- $\beta = 200$



4) BJT: AC Analysis: Determine the 2-port model for the following CE amplifier.

rf 1000 + 100*mo + day	Rin	Ain	Rout	Ao



5) 2-Port model (experimental): Determine the 2-port parameters based upon the following experimental data:

Case 1:

- $V_{in} = 1\text{mV}$ @ 1kHz
- $R_1 = 0 \text{ Ohms}$
- $R_2 = 10\text{M Ohms}$

results in $V_{out} = 173\text{mV}$

Case 2:

- $V_{in} = 1\text{mV}$ @ 1kHz
- $R_1 = X \text{ Ohms}$
- $R_2 = 10\text{M Ohms}$

results in $V_{out} = 100\text{mV}$

Case 3

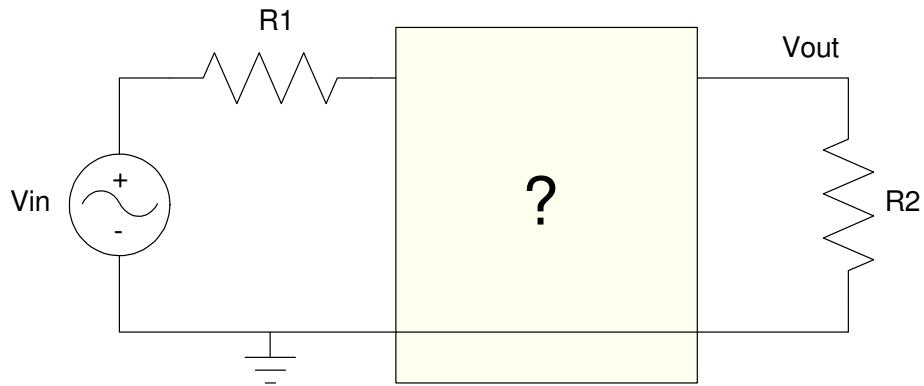
- $V_{in} = 1\text{mV}$ @ 1kHz
- $R_1 = 0 \text{ Ohms}$
- $R_2 = X \text{ Ohms}$

results in $V_{out} = 50\text{mV}$

Assume

- $X = 1000 + 100*(\text{your birth month}) + (\text{your birth date}) \text{ Ohms}$
- $A_i = 0$

X $1000 + 100*\text{mo} + \text{day}$	R_{in}	A_i	R_{out}	A_o
		0		



6) Determine the 2-port model for the following cascaded CE amplifier

R 1000 + 100*mo + day	Rin	Ai	Rout	Ao

